

(e) exposing said second mask image segment with radiation using said imaging tool to produce a second pattern edge gradient, said second pattern edge gradient defining said second edge of said feature in said material, wherein said first and second edges are separated by a distance which is less than or equal to the Rayleigh limit of said imaging tool;

(f) developing said radiation-sensitive material, thereby reproducing said two-dimensional feature on said substrate.

12. (Twice Amended) In a process for fabricating semiconductor devices, a method of lithographically printing a rectangular feature into a photoresist layer deposited over a semiconductor substrate, said rectangular feature having at least two closely-spaced opposing feature edges, said method comprising the steps of:

decomposing said rectangular feature into a rectangular mask image having a pair of opposing mask edges of a length which is greater than or equal to the length of said opposing feature edges, said opposing mask edges being spaced apart a predetermined distance which is greater than the spacing between said opposing feature edges;

exposing a first one of said mask edges with radiation using an imaging tool to produce a first pattern edge gradient which defines a first one of said feature edges in said photoresist layer;

offsetting said rectangular mask image relative to said substrate;

exposing the second one of said mask edges with radiation using an imaging tool to produce a second pattern edge gradient defining the second one of said feature edges in said photoresist layer, wherein said spacing between said opposing feature edges is less than or equal to the Rayleigh limit of said imaging tool.